

Product Summary

- $V_{DS} = -20V, I_D = -2A$
- $R_{DS(ON)} < 70m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} < 110m\Omega @ V_{GS} = -2.5V$

Application

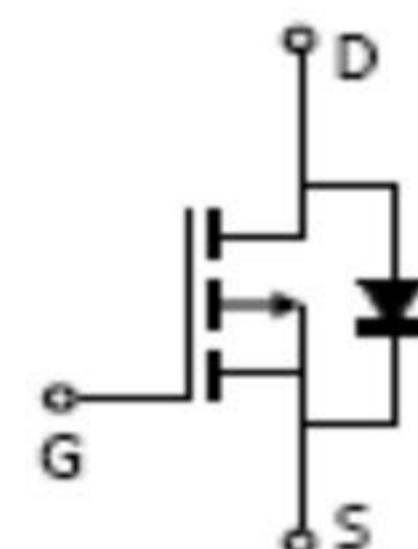
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Circuit diagram



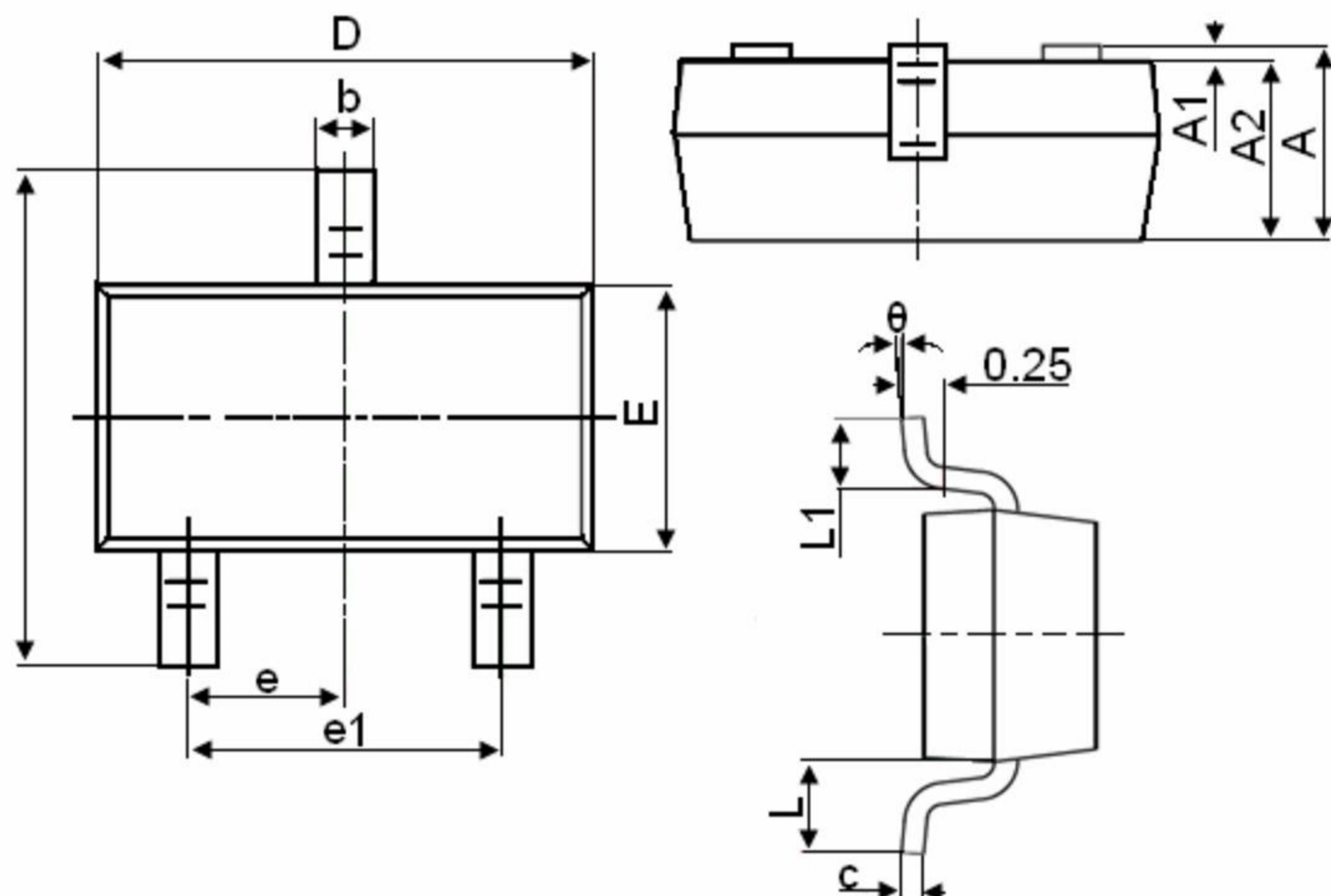
Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	-2	A
Pulsed Diode Current	I_{DM}	-10	
Power Dissipation	PD	1.1	W
Thermal Resistance from Junction to Ambient ($t \leq 10s$)	$R_{\theta JA}$	250	°C/W
Operating Junction	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	$V_{GS} = 0\text{V}, ID = -250\mu\text{A}$	-20			V
Gate-source threshold voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, ID = -250\mu\text{A}$	-0.4		-1.5	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{V}, V_{GS} = \pm 8\text{V}$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$			-1	μA
Drain-source on-state resistancea	RDS(on)	$V_{GS} = -4.5\text{V}, ID = -2\text{A}$		52	70	$\text{m}\Omega$
		$V_{GS} = -2.5\text{V}, ID = -1.7\text{A}$		78	110	$\text{m}\Omega$
		$V_{GS} = -1.8\text{V}, ID = -1.2\text{A}$			210	$\text{m}\Omega$
Forward transconductancea	g_{fs}	$V_{DS} = -4.5\text{V}, ID = -2\text{A}$		8		S
Diode forward voltage	V_{SD}	$IS = -1\text{A}, V_{GS} = 0\text{V}$		-0.8	-1.2	V
Dynamic						
Input capacitance	C_{iss}	$V_{DS} = -10\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		600		pF
Output capacitance	C_{oss}			175		pF
Reverse transfer capacitanceb	C_{rss}			80		pF
Total gate charge	Q_g	$V_{DS} = -10\text{V}, V_{GS} = -4.5\text{V}, ID = -2\text{A}$		8		nC
Gate-source charge	Q_{gs}			1.3		nC
Gate-drain charge	Q_{gd}			2.2		nC
Gate resistance	R_g	$f = 1\text{MHz}$	0.5		3.2	Ω
Switchingbtr						
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -10\text{V}$ $RL = 3.5\Omega, ID \approx -1\text{A}$, $V_{GEN} = -4.5\text{V}, R_g = 3\Omega$		6		ns
Rise time	t_r			9		ns
Turn-off delay time	$t_{d(off)}$			31		ns
Fall time	t_f			26		ns
Drain-source body diode characteristicstr						
Continuous Source-Drain Diode Current	I_S	$T_c = 25^\circ\text{C}$			-1.2	A
Pulsed Diode forward Current	I_{SM}				-10	A

SOT-23 Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°